HZU6.2Z

Silicon Epitaxial Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-581(Z)
Rev 0

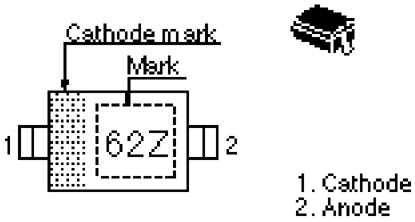
Features

- Low capacitance (C = 8.5pF max) and can protect ESD of signal line.
- Ultra small Resin Package (URP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HZU6.2Z	62Z	URP

Outline



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semiconductor

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd [*1]	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Note: 1. Two device total, See Fig.2.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V_Z	5.90	—	6.50	V	I_Z = 5 mA, 40ms pulse
Reverse current	I_R	—	—	3	µA	V_R = 5.5V
Capacitance	C	—	8.0	8.5	pF	V_R = 0V, f = 1 MHz
Dynamic resistance	r_d	—	—	60	Ω	I_Z = 5 mA

Main Characteristic

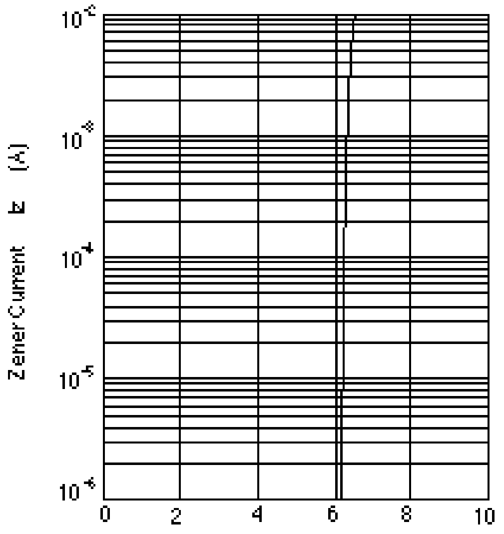


Fig.1 Zener current Vs. Zener voltage

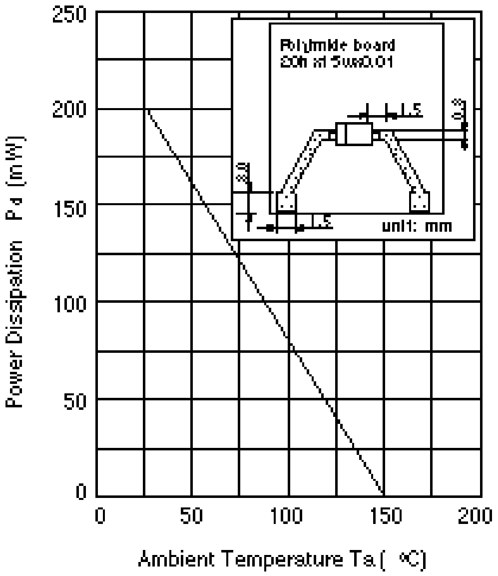


Fig.2 Power Dissipation Vs. Ambient Temperatur

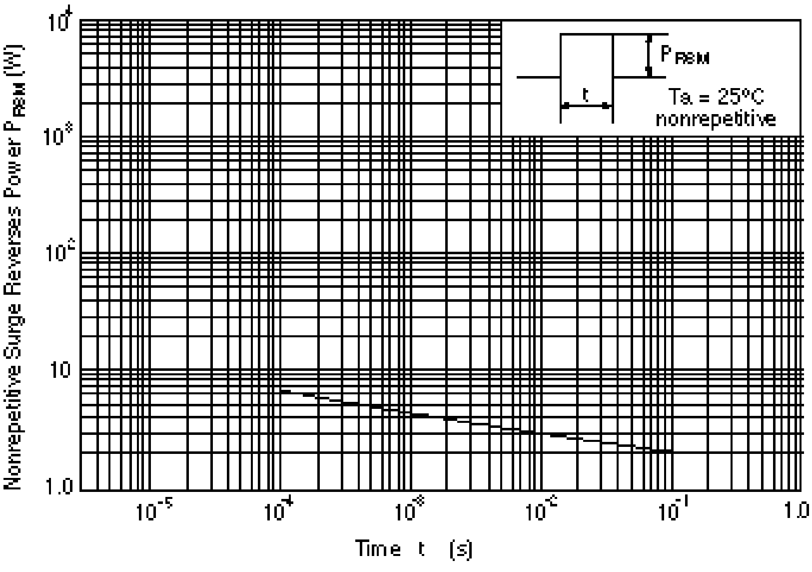


Fig.3 Surge Reverse Power Ratings

Main Characteristic

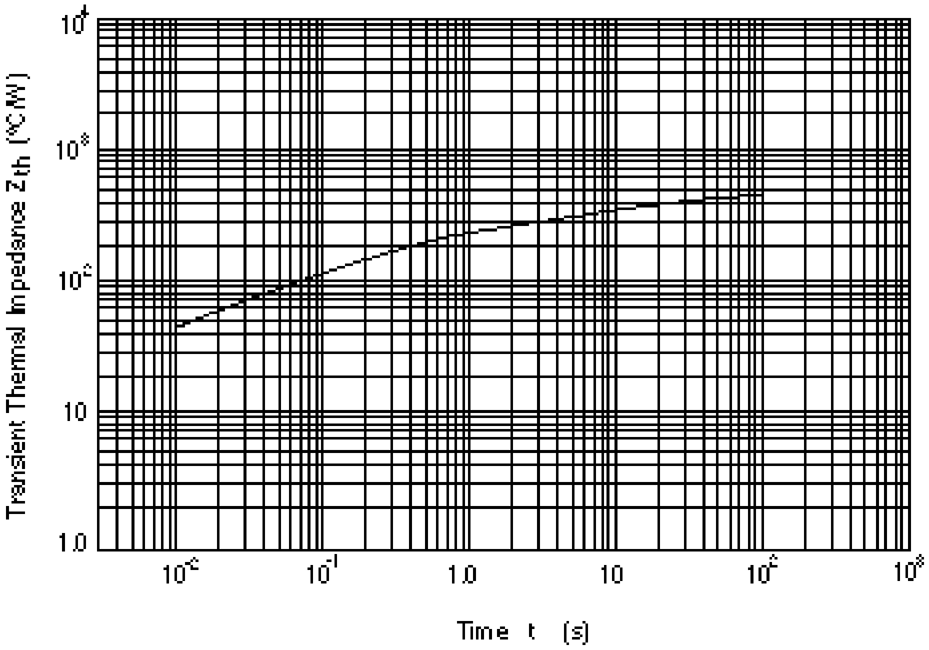
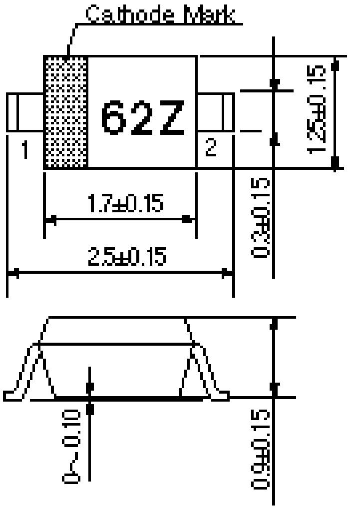


Fig.4 Transient Thermal Impedance

Package Dimensions

Unit : mm



1. Cathode
2. Anode

Hitachi Code	URP
JEDEC Code	—
EIAJ Code	—
Weight(g)	0.004